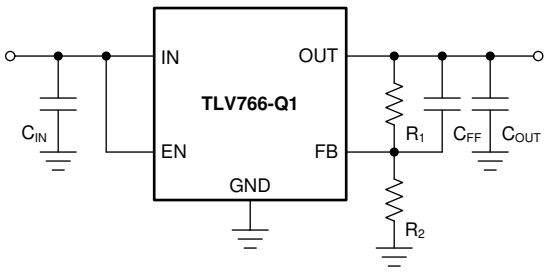
# TLV766-Q1 500mA、16V 线性稳压器

## 1 特性

- 符合面向汽车应用的 AEC-Q100 标准：
  - 温度等级 1：–40°C 至 +125°C，$T_A$
  - 结温：–40°C 至 +150°C，$T_J$
- 输入电压范围：2.5V 至 16V（最大 18V）
- 输出电压范围：
  - 0.8V 至 14.6V（可调节）
  - 1.2V 至 12V（固定）
- 在整个负载和温度范围内的输出精度为 1%
- 低静态电流 ($I_Q$)：
  - 空载时典型值为 50µA
  - 禁用时最大值为 4 µ A
- 高 PSRR：1kHz 频率下为 70dB，1MHz 频率下为 46dB
- 内部软启动时间：500µs（典型值）
- 折返电流限制和热保护
- 与 1µF 或更大的电容器搭配使用时可保持稳定
- 功能安全型
  - 可帮助进行功能安全系统设计的文档
- 封装：具有可湿性侧面的 8 引脚、3mm × 3mm WSON 封装
  - 低热阻 ($R_{\theta JA}$)：51.9°C/W

## 2 应用

- 直流/直流转换器
- 逆变器和电机控制
- 车载充电器 (OBC) 和无线充电器
- 汽车音响主机




典型应用电路

## 3 说明

TLV766-Q1 是一款具有宽输入范围的线性稳压器，支持 2.5V 至 16V 的输入电压和高达 500mA 的负载电流。输出范围为 0.8V 至 12V，在可调节版本中输出可高达 14.6V。

该器件具有宽输入电压范围，因此可由变压器次级绕组和稳压电源轨（例如 10V 或 12V）供电。此外，该器件还具有宽输出电压范围，不仅可为碳化硅 (SiC) 栅极驱动器和麦克风产生偏置电压，还能为微控制器 (MCU) 和处理器供电。

TLV766-Q1 具有 1% 的输出精度，可为电源要求严格的数字负载供电。

内部软启动电路可减小启动期间的浪涌电流，从而降低输入电容。

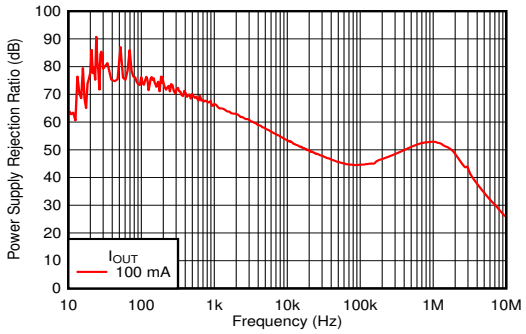
高带宽 PSRR 性能在 1kHz 时大于 70dB，在 1MHz 时大于 46dB，因此有助于衰减上游直流/直流转换器的开关频率，并最大限度减少后置稳压器滤波。该器件具有 20Hz 至 20kHz 的高纹波抑制，是为音频组件供电的理想选择。

TLV766-Q1 采用具有可湿性侧面和低热阻的 8 引脚、3mm × 3mm VSON (DRB) 封装。

**封装信息**

| 器件型号 | 封装(1) | 封装尺寸（标称值） |
|---|---|---|
| TLV766-Q1 | DRB (VSON, 8) | 3.00mm × 3.00mm |

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。




PSRR 性能

本文档旨在为方便起见，提供有关 TI 产品中文版本的信息，以确认产品的概要。有关适用的官方英文版本的最新信息，请访问 www.ti.com，其内容始终优先。TI 不保证翻译的准确性和有效性。在实际设计之前，请务必参考最新版本的英文版本。

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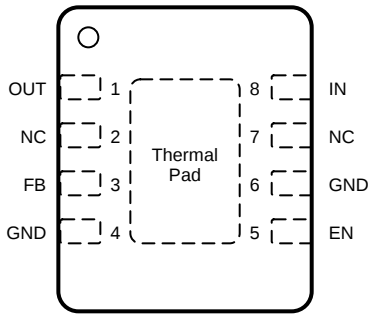
## 4 Revision History

注：以前版本的页码可能与当前版本的页码不同

| Changes from Revision * (December 2020) to Revision A (October 2022) | Page |
|---|---|
| • 向*特性* 部分添加了功能安全的项目符号 | 1 |

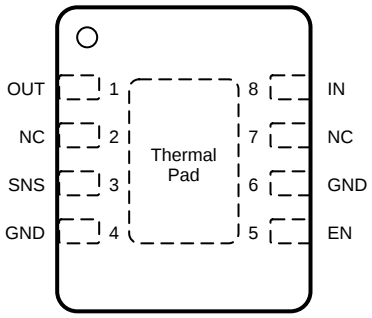

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## 5 Pin Configuration and Functions




Not to scale

**图 5-1. DRB Package (Adjustable Version), 8-Pin WSON (Top View)**




Not to scale

**图 5-2. DRB Package (Fixed Version), 8-Pin WSON (Top View)**

**表 5-1. Pin Functions**

| PIN | | | TYPE | DESCRIPTION |
|---|---|---|---|---|
| NAME | DRB (Adjustable) | DRB (Fixed) | | |
| EN | 5 | 5 | Input | Enable pin. Driving the enable pin high enables the device. Driving this pin low disables the device. High and low thresholds are listed in the *Electrical Characteristics* table. This pin has an internal pullup resistor and can be left floating to enable the device or the pin can be connected to the input pin. |
| FB | 3 | — | Input | Feedback pin. Input to the control-loop error amplifier. This pin is used to set the output voltage of the device with the use of external resistors. Do not float this pin. For adjustable-voltage version devices only. |
| GND | 4, 6 | 4, 6 | — | Ground pin. All ground pins must be grounded. |
| NC | 2, 7 | 2, 7 | — | NC pin. Not internally connected. This pin can be either floated or connected to GND for best thermal performance. |
| IN | 8 | 8 | Input | Input pin. Use the recommended capacitor value as listed in the *Recommended Operating Conditions* table. Place the input capacitor as close to the IN and GND pins of the device as possible. |
| OUT | 1 | 1 | Output | Output pin. Use the recommended capacitor value as listed in the *Recommended Operating Conditions* table. Place the output capacitor as close to the OUT and GND pins of the device as possible. |
| SNS | — | 3 | Input | Output sense pin. Connect the SNS pin to the OUT pin, or to remotely sense the output voltage at the load, connect the SNS pin to the load. Do not float this pin. For fixed-voltage version devices only. |
| Thermal pad | | | — | Exposed pad of the package. Connect this pad to ground or leave floating. Connect the thermal pad to a large-area ground plane for best thermal performance. |

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# 6 Specifications

## 6.1 Absolute Maximum Ratings

Over operating free-air temperature range (unless otherwise noted)(1)

| | | MIN | MAX | UNIT |
|---|---|---|---|---|
| Voltage(2) | Input pin, IN | –0.3 | 18 | V |
| | Output pin, OUT(3) | –0.3 | $V_{IN}$ + 0.3 | |
| | Sense pin, SNS(3) | –0.3 | $V_{IN}$ + 0.3 | |
| | Feedback pin, FB | –0.3 | 3 | |
| | Enable pin, EN | –0.3 | 18 | |
| Current | Maximum output current | Internally limited | | A |
| Temperature | Ambient ($T_A$) | –40 | 125 | °C |
| | Operating junction ($T_J$) | –50 | 150 | |
| | Storage ($T_{STG}$) | –65 | 150 | |

(1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltages with respect to GND.
(3) $V_{IN}$ + 0.3 V or 18 V (whichever is smaller).

## 6.2 ESD Ratings

| | | | | VALUE | UNIT |
|---|---|---|---|---|---|
| $V_{(ESD)}$ | Electrostatic discharge | Human body model (HBM), per AEC Q100-002(1) | | ±2000 | V |
| | | Charged-device model (CDM), per AEC Q100-011 | All pins | ±500 | |
| | | | Corner pins | ±750 | |

(1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.


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## 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

| | | MIN | NOM | MAX | UNIT |
|---|---|---|---|---|---|
| $V_{IN}$ | Input voltage | 2.5 | | 16 | V |
| $V_{EN}$ | Enable voltage | 0 | | 16 | V |
| $V_{OUT}$ | Output voltage | 0.8 | | 14.6 | V |
| $I_{OUT}$ | Output current | 0 | | 500 | mA |
| $C_{OUT}$ | Output capacitor(1) | 1 | 2.2 | 220 | µF |
| $C_{OUT}$ ESR | Output capacitor ESR | 2 | | 500 | mΩ |
| $C_{IN}$ | Input capacitor | | 1 | | µF |
| $C_{FF}$ | Feed-forward capacitor (optional(2), for adjustable device only) | | 10 | | pF |
| $I_{FB_DIVIDER}$ | Feedback divider current(2) (adjustable device only) | 5 | | | µA |
| $T_A$ | Ambient temperature range | –40 | | 125 | °C |
| $T_J$ | Junction temperature range | –40 | | 150 | °C |

(1) Effective output capacitance of 0.5 µF minimum required for stability.
(2) $C_{FF}$ required for stability if the feedback divider current < 5 µA. Feedback divider current = $V_{OUT}$ / ($R_1$ + $R_2$). See the *Feed-Forward Capacitor ($C_{FF}$)* section for details.

## 6.4 Thermal Information

| THERMAL METRIC(1) | | TLV766-Q1 DRB (VSON) 8 PINS | UNIT |
|---|---|---|---|
| $R_{\theta JA}$ | Junction-to-ambient thermal resistance | 51.9 | °C/W |
| $R_{\theta JC(top)}$ | Junction-to-case (top) thermal resistance | 66.2 | °C/W |
| $R_{\theta JB}$ | Junction-to-board thermal resistance | 24.4 | °C/W |
| $\Psi_{JT}$ | Junction-to-top characterization parameter | 2.7 | °C/W |
| $\Psi_{JB}$ | Junction-to-board characterization parameter | 24.3 | °C/W |
| $R_{\theta JC(bot)}$ | Junction-to-case (bottom) thermal resistance | 6.9 | °C/W |

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

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## 6.5 Electrical Characteristics

specified at $T_J$ = –40°C to 150°C, $V_{IN}$ = $V_{OUT(nom)}$ + 1.5 V or $V_{IN}$ = 2.5 V (whichever is greater), FB/SNS tied to OUT, $I_{OUT}$ = 10 mA, $V_{EN}$ = 2 V, $C_{IN}$ = 1.0 µF, and $C_{OUT}$ = 1.0 µF (unless otherwise noted); typical values are at $T_J$= 25ºC

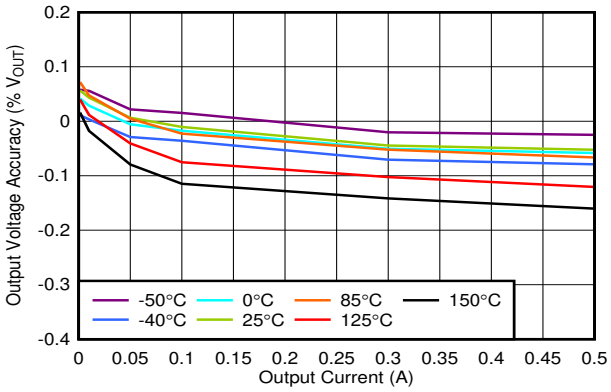
| PARAMETER | | TEST CONDITIONS | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|
| $V_{OUT}$ | Output accuracy | $T_J$ = 25°C | | –0.5 | | 0.5 | % |
| | | $T_J$ = –40°C to 150°C | $V_{IN} \geq$ 2.5 V, 1 mA $\leq I_{OUT} \leq$ 500 mA | –1 | | 1 | |
| $V_{FB}$ | Feedback voltage | | | | 0.8 | | V |
| $V_{REF}$ | Internal reference (adjustable device) | $T_J$ = 25°C | | –0.5 | | 0.5 | % |
| | | $T_J$ = –40°C to 150°C | | –1 | | 1 | |
| $I_{FB}$ | Feedback pin current | $V_{FB}$ = 1 V | | –20 | 1 | 50 | nA |
| $\Delta V_{OUT(\Delta VIN)}$ | Line regulation(1) | $V_{OUT(NOM)}$ +1.5 V $\leq V_{IN} \leq$ 16 V, $I_{OUT}$ = 10 mA | | | | 0.02 | %/V |
| $\Delta V_{OUT(\Delta IOUT)}$ | Load regulation | 1 mA $\leq I_{OUT} \leq$ 500 mA | | –0.5 | 0.1 | 0.5 | %/A |
| $V_{DO}$ | Dropout voltage(2) | $I_{OUT}$ = 500 mA | | 0.3 | | 0.75 | |
| $I_{CL}$ | Output current limit | $V_{OUT}$ = 0.9 x $V_{OUT(NOM)}$ | | 0.55 | 0.7 | 0.8 | A |
| $I_{SC}$ | Short-circuit current limit | $V_{OUT}$ = 0 V | | 50 | 125 | 200 | mA |
| $I_Q$ | Quiescent current | Adjustable output device, $I_{OUT}$ = 0 mA | | 25 | 50 | 80 | µA |
| | | Fixed output devices, $I_{OUT}$ = 0 mA | | 25 | 60 | 95 | |
| $I_{SHUTDOWN}$ | Shutdown current | $V_{EN} \leq$ 0.4 V, $V_{IN}$ = 16 V | | 0.1 | 1.6 | 4 | µA |
| $V_{EN(HIGH)}$ | Enable pin logic high | 2.5 V $\leq V_{IN} \leq$ 16 V | | 1.2 | | | V |
| $V_{EN(LOW)}$ | Enable pin logic low | 2.5 V $\leq V_{IN} \leq$ 16 V | | | | 0.4 | V |
| $I_{EN}$ | Enable pullup current | $V_{EN}$ = 0 V | | 200 | 400 | 800 | nA |
| $I_{PULLDOWN}$ | Output pulldown current | $V_{IN}$ = 16 V, $V_{OUT}$ = 2.5 V, $V_{EN}$ = 0 V | | 0.9 | 1.4 | 1.6 | mA |
| PSRR | Power-supply rejection ratio | $V_{IN}$ = 3.3 V, $V_{OUT}$ = 1.8 V, $I_{OUT}$ = 300 mA, f = 120 Hz | | | 70 | | dB |
| $V_n$ | Output noise voltage | BW = 10 Hz to 100 kHz, $V_{IN}$ = 3.3 V, $V_{OUT}$ = 0.8 V, $I_{OUT}$ = 100 mA | | | 60 | | $\mu V_{RMS}$ |
| $V_{UVLO+}$ | UVLO threshold rising | $V_{IN}$ rising | | 2 | 2.22 | 2.4 | V |
| $V_{UVLO-}$ | UVLO threshold falling | $V_{IN}$ falling | | 1.9 | 2.09 | 2.3 | V |
| $V_{UVLO(HYS)}$ | UVLO hysteresis | | | 100 | 130 | 200 | mV |
| $T_{SD(shutdown)}$ | Thermal shutdown temperature | Temperature increasing | | | 180 | | ºC |
| $T_{SD(reset)}$ | Thermal shutdown reset temperature | Temperature falling | | | 160 | | ºC |

(1) Line regulation is measured with $V_{IN}$ = $V_{OUT(NOM)}$ + 1.5 V or 2.5 V (whichever is greater).
(2) $V_{DO}$ is measured with $V_{IN}$ = 95% x $V_{OUT(nom)}$ for fixed output devices. $V_{DO}$ is not measured for fixed output devices when $V_{OUT}$ < 2.5 V. For the adjustable output device, $V_{DO}$ is measured with $V_{FB}$ = 95% x $V_{FB(nom)}$ and $V_{IN}$ = 2.5 V.


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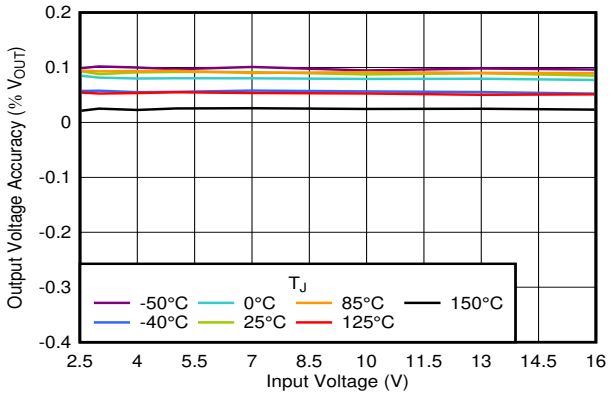
## 6.6 Typical Characteristics

at operating temperature $T_J$ = 25°C, $V_{IN}$ = $V_{OUT(NOM)}$ + 1.5 V or 2.5 V (whichever is greater), $I_{OUT}$ = 10 mA, $V_{EN}$ = 2.0 V, $C_{IN}$ = 1.0 µF, and $C_{OUT}$ = 1.0 µF (unless otherwise noted)




$V_{IN}$ = 2.5 V

**图 6-1. $V_{OUT}$ Accuracy vs $I_{OUT}$**




$I_{OUT}$ = 10 mA

**图 6-2. $V_{OUT}$ Accuracy vs $V_{IN}$**

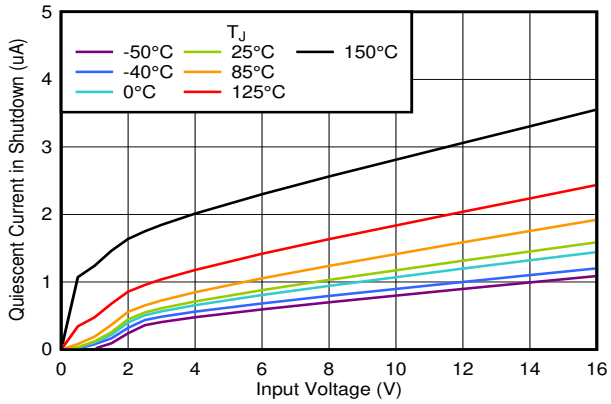
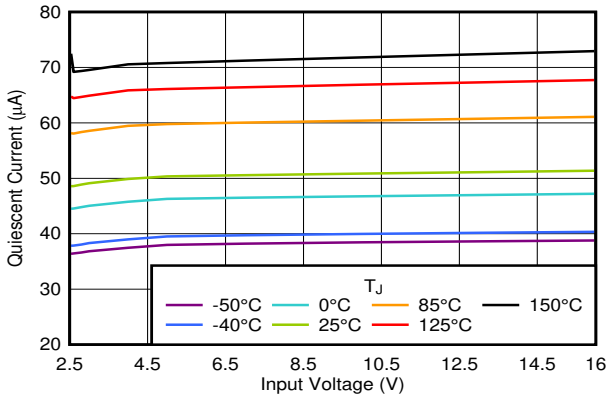
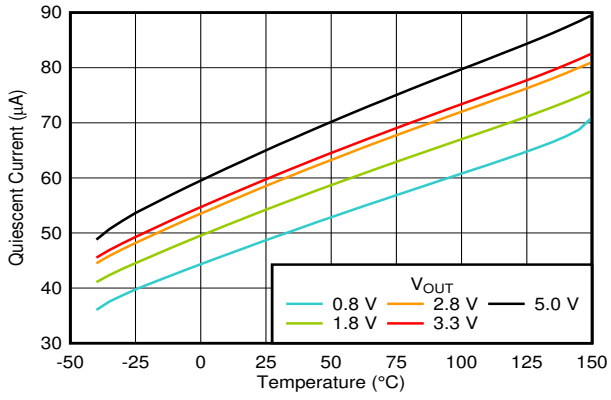



**图 6-3. $I_{SHUTDOWN}$ vs $V_{IN}$**



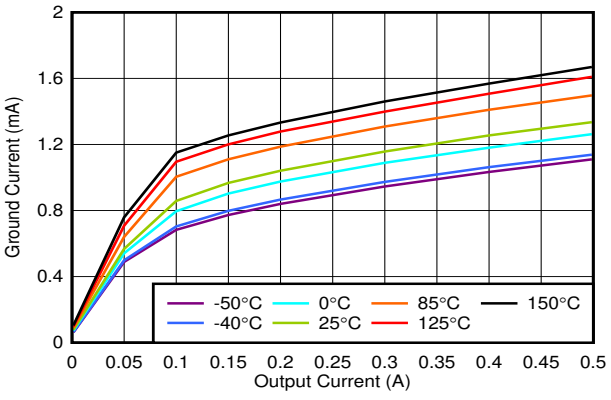

$I_{OUT}$ = 0 mA, adjustable-voltage version devices

**图 6-4. $I_Q$ vs $V_{IN}$**




$I_{OUT}$ = 0 mA, fixed-voltage version devices

**图 6-5. $I_Q$ vs Temperature**



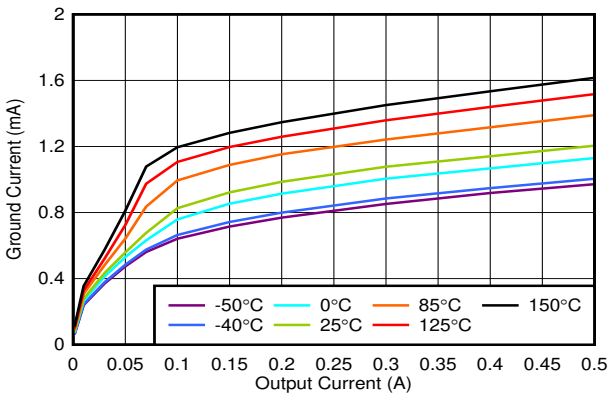

$V_{IN}$ = 5 V

**图 6-6. $I_{GND}$ vs $I_{OUT}$**

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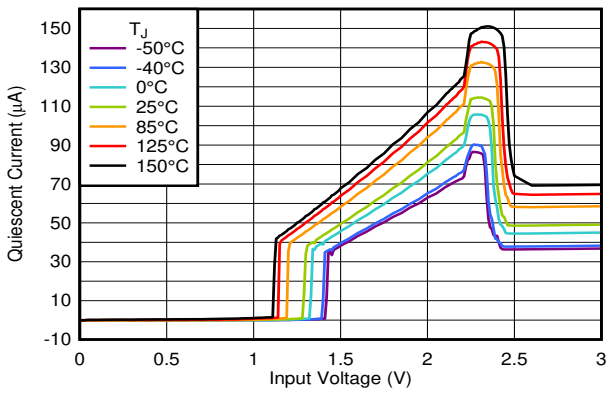
## 6.6 Typical Characteristics (continued)

at operating temperature $T_J$ = 25°C, $V_{IN}$ = $V_{OUT(NOM)}$ + 1.5 V or 2.5 V (whichever is greater), $I_{OUT}$ = 10 mA, $V_{EN}$ = 2.0 V, $C_{IN}$ = 1.0 µF, and $C_{OUT}$ = 1.0 µF (unless otherwise noted)



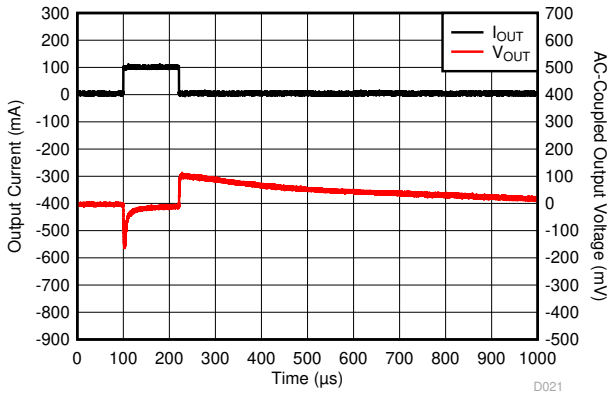

$V_{IN}$ = 2.5 V

**图 6-7. $I_{GND}$ vs $I_{OUT}$**



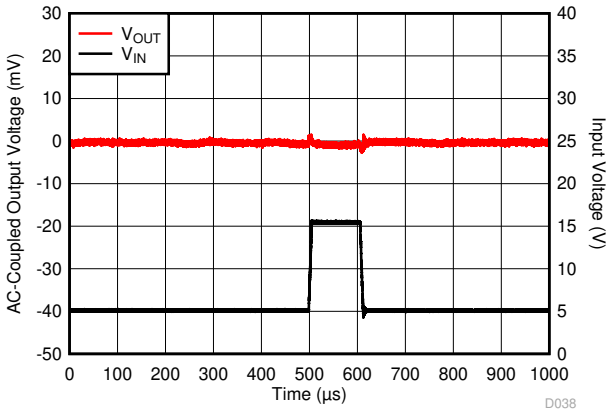

$I_{OUT}$ = 0 mA

**图 6-8. $I_Q$ Increase Below Minimum $V_{IN}$**



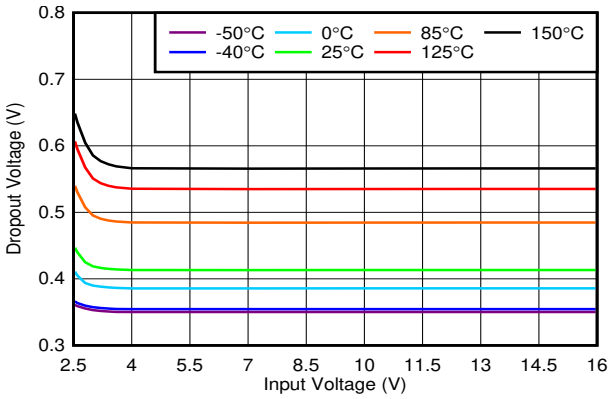

$V_{IN}$ = 5 V, $V_{OUT}$ = 3.3 V, $C_{FF}$ = 10 pF, ramp rate = 0.4 A/µs

**图 6-9. $I_{OUT}$ Transient From 0 mA to 100 mA**



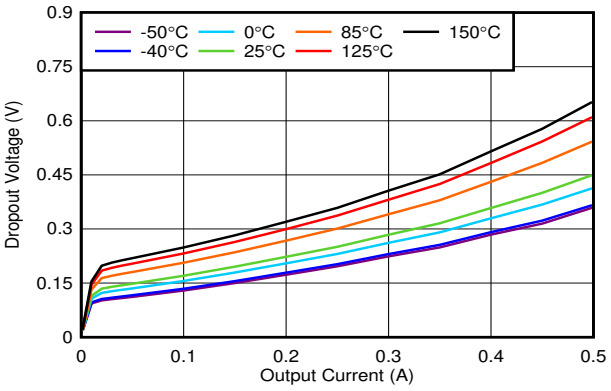

$V_{OUT}$ = 3.3 V, $I_{OUT}$ = 33 µA, $V_{IN}$ ramp rate = 1.6 V/µs

**图 6-10. $V_{IN}$ Transient From 5 V to 16 V**




$I_{OUT}$ = 0.5 A

**图 6-11. $V_{DO}$ vs $V_{IN}$**



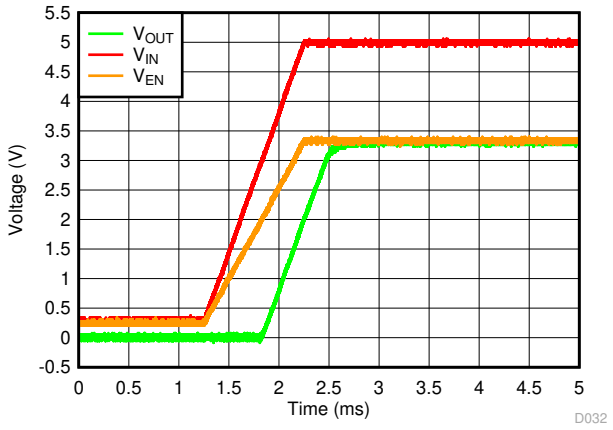

$V_{IN}$ = 2.5 V

**图 6-12. $V_{DO}$ vs $I_{OUT}$**


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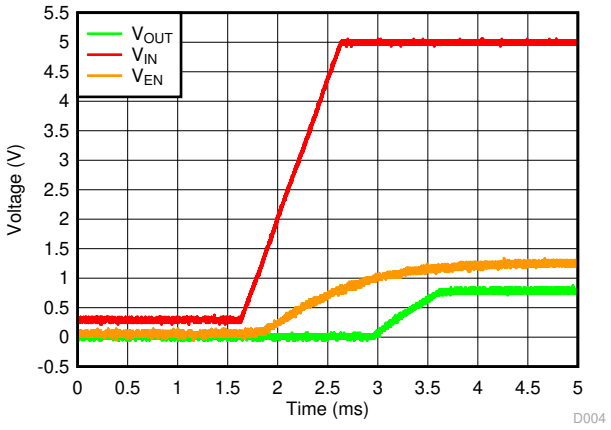
## 6.6 Typical Characteristics (continued)

at operating temperature $T_J$ = 25°C, $V_{IN}$ = $V_{OUT(NOM)}$ + 1.5 V or 2.5 V (whichever is greater), $I_{OUT}$ = 10 mA, $V_{EN}$ = 2.0 V, $C_{IN}$ = 1.0 µF, and $C_{OUT}$ = 1.0 µF (unless otherwise noted)



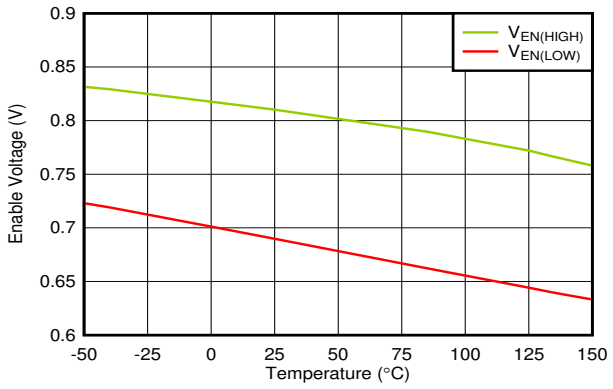

$V_{OUT}$ = 3.3 V

**图 6-13. Startup With Separate $V_{EN}$ and $V_{IN}$**



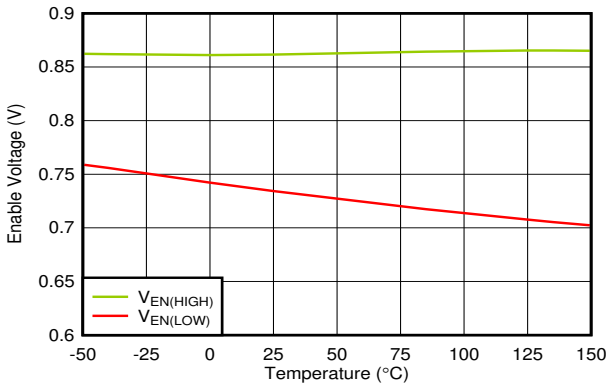

EN pulled up internally, $V_{OUT}$ = 0.8 V

**图 6-14. Startup With $V_{EN}$ Floating**




$V_{IN}$ = 2.5 V

**图 6-15. $V_{EN}$ Thresholds vs Temperature**




$V_{IN}$ = 16 V

**图 6-16. $V_{EN}$ Thresholds vs Temperature**

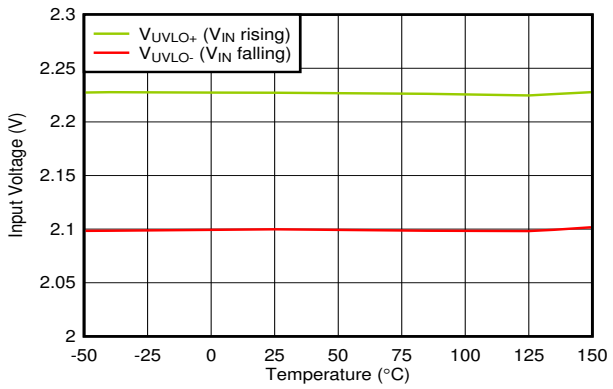
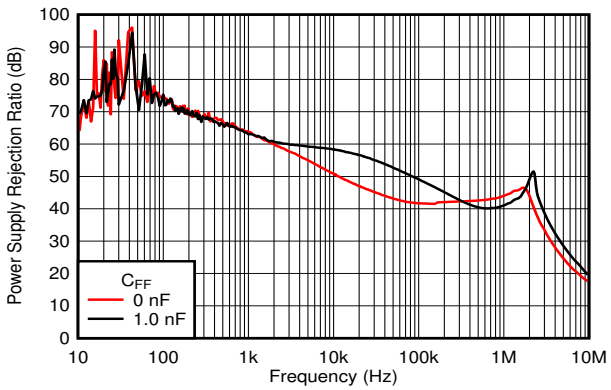



**图 6-17. UVLO Thresholds vs Temperature**



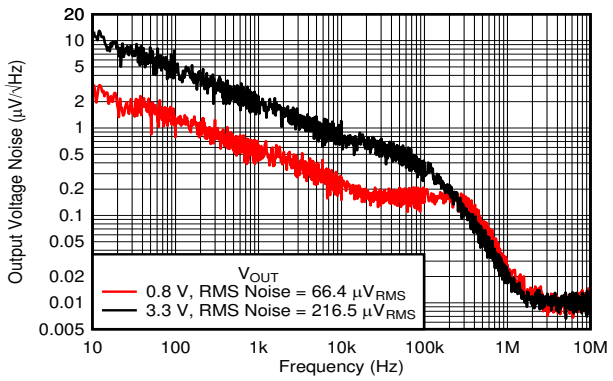

$V_{OUT}$ = 3.3 V, $V_{IN}$ = 4.8 V, $I_{OUT}$ = 0.33 A

**图 6-18. PSRR vs Frequency and $C_{FF}$**

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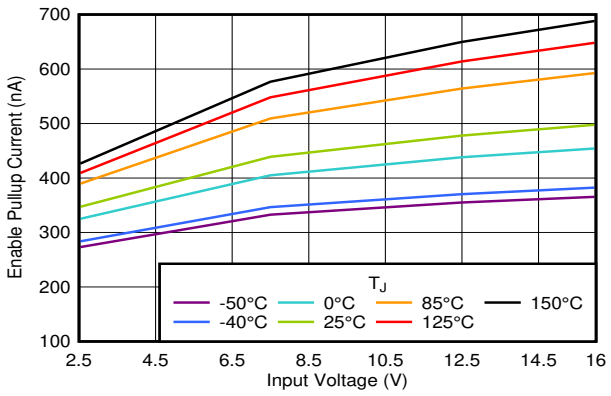
## 6.6 Typical Characteristics (continued)

at operating temperature $T_J$ = 25°C, $V_{IN}$ = $V_{OUT(NOM)}$ + 1.5 V or 2.5 V (whichever is greater), $I_{OUT}$ = 10 mA, $V_{EN}$ = 2.0 V, $C_{IN}$ = 1.0 µF, and $C_{OUT}$ = 1.0 µF (unless otherwise noted)



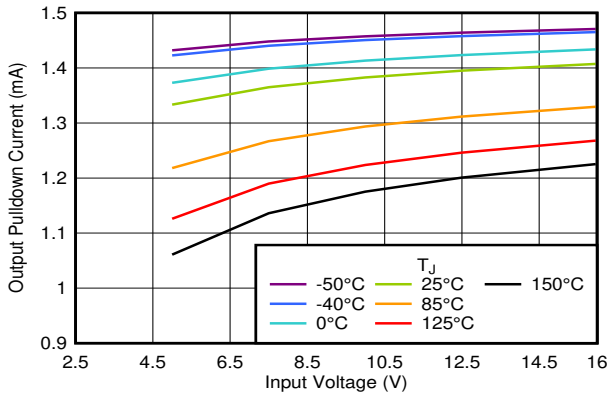

$C_{FF}$ = 0 nF, $I_{OUT}$ = 0.1 A, RMS noise BW = 10 Hz to 100 kHz

**图 6-19. Output Noise ($V_n$) vs Frequency and $V_{OUT}$**



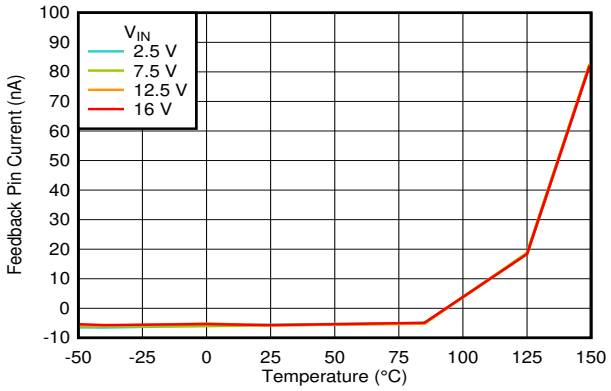

$V_{EN}$ = 0 V

**图 6-20. $I_{EN}$ vs $V_{IN}$**



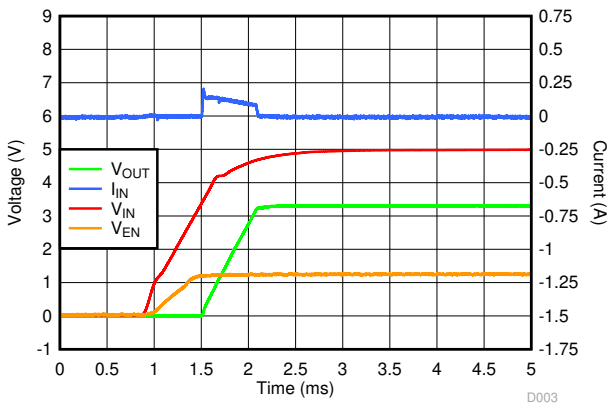

$V_{OUT}$ = 2.5 V

**图 6-21. $I_{PULLDOWN}$ vs $V_{IN}$**



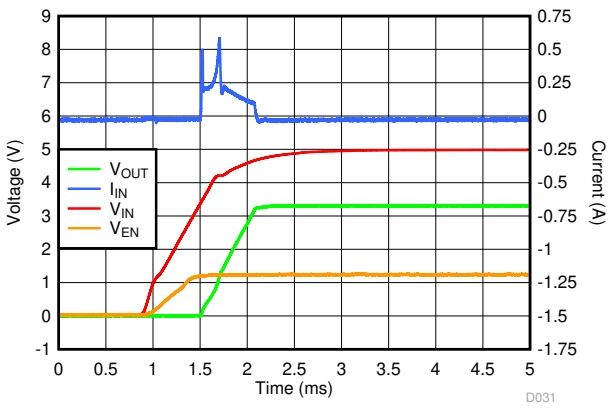

$V_{FB}$ = 1.0 V

**图 6-22. $I_{FB}$ vs Temperature**




$V_{OUT}$ = 3.3 V, $I_{OUT}$ = 33 µA

**图 6-23. Startup Inrush Current With $C_{OUT}$ = 22 µF**




$V_{OUT}$ = 3.3 V, $I_{OUT}$ = 33 µA

**图 6-24. Startup Inrush Current With $C_{OUT}$ = 47 µF**


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# 7 Detailed Description

## 7.1 Overview

The TLV766-Q1 is a low quiescent current, high PSRR linear regulator capable of handling up to 500 mA of load current. Unlike typical high current linear regulators, the TLV766-Q1 consumes significantly less quiescent current. This device is ideal for high current applications that require very sensitive power-supply rails.

This device features an integrated foldback current limit, thermal shutdown, output enable, internal output pulldown, and undervoltage lockout (UVLO). This device delivers excellent line and load transient performance. This device is low noise and exhibits very good PSRR. The operating ambient temperature range of the device is –40°C to +125°C.

## 7.2 Functional Block Diagrams

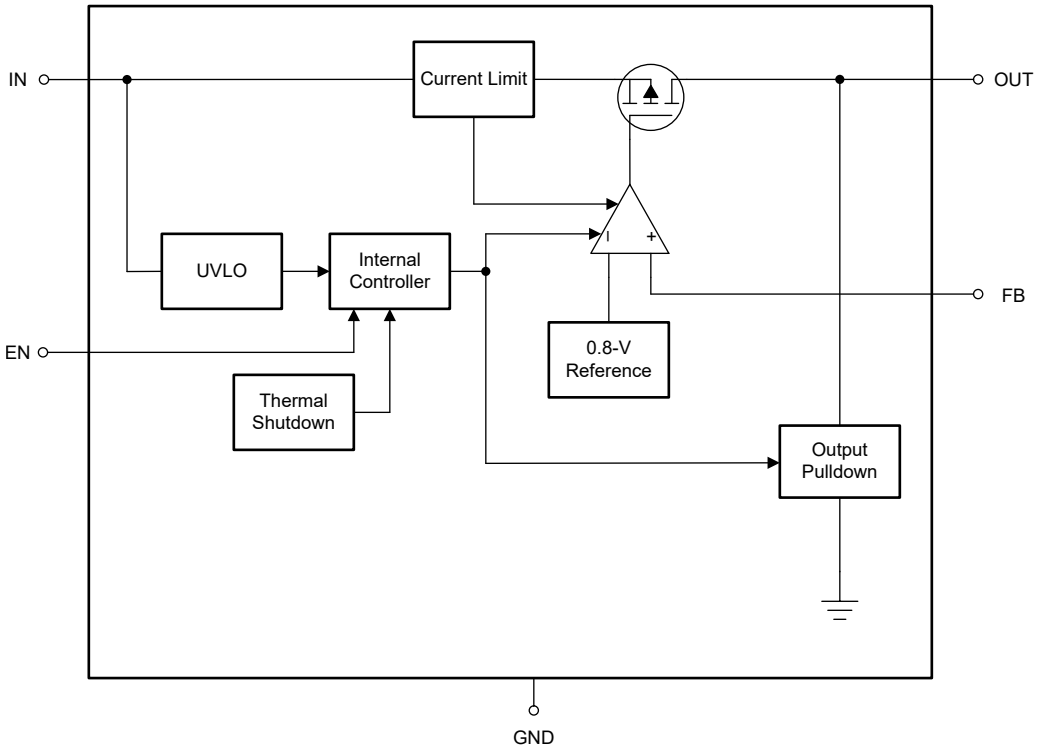



**图 7-1. Adjustable-Version Block Diagram**

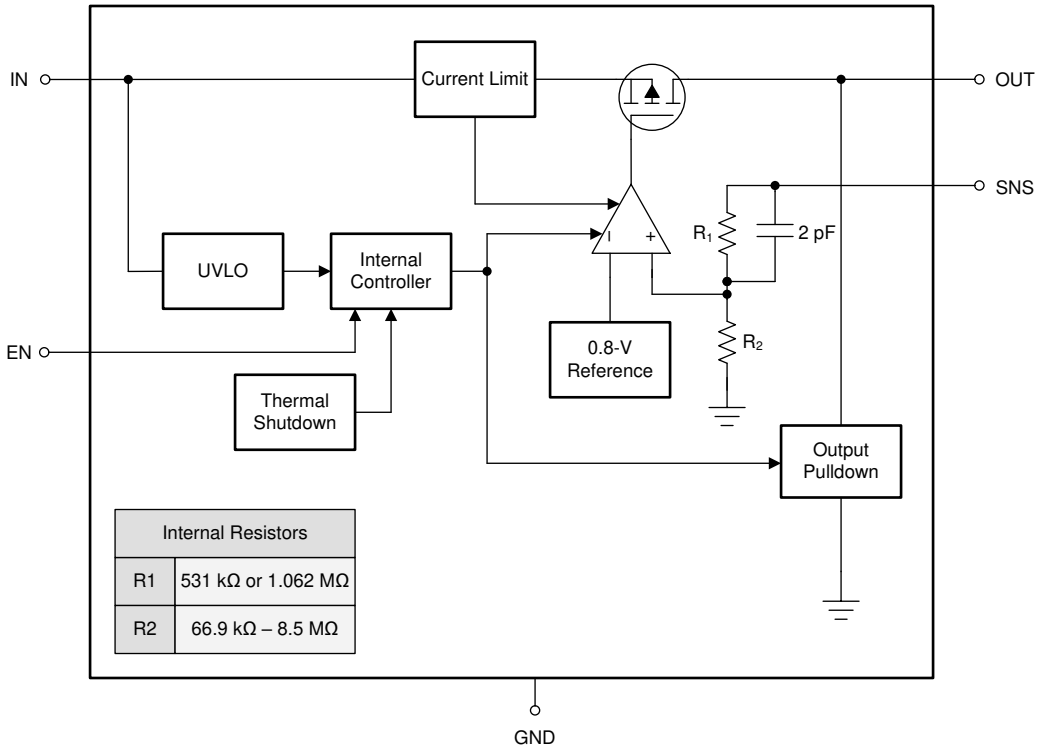



**图 7-2. Fixed-Version Block Diagram**

## 7.3 Feature Description

### 7.3.1 Output Enable

The enable pin for the device is an active-high pin. The output voltage is enabled when the voltage of the enable pin is greater than the high-level input voltage of the EN pin and disabled with the enable pin voltage is less than the low-level input voltage of the EN pin. If independent control of the output voltage is not needed, connect the enable pin to the input of the device.

This device has an internal pullup current on the EN pin. The EN pin can be left floating to enable the device.

The device has an internal pulldown circuit that activates when the device is disabled to actively discharge the output voltage.

### 7.3.2 Dropout Voltage

Dropout voltage ($V_{DO}$) is defined as the input voltage minus the output voltage ($V_{IN} - V_{OUT}$) at the rated output current ($I_{RATED}$), where the pass transistor is fully on. $I_{RATED}$ is the maximum $I_{OUT}$ listed in the *Recommended Operating Conditions* table. The pass transistor is in the ohmic or triode region of operation, and acts as a switch. The dropout voltage indirectly specifies a minimum input voltage greater than the nominal programmed output voltage at which the output voltage is expected to stay in regulation. If the input voltage falls to less than the nominal output regulation, then the output voltage falls as well.

For a CMOS regulator, the dropout voltage is determined by the drain-source on-state resistance ($R_{DS(ON)}$) of the pass transistor. Therefore, if the linear regulator operates at less than the rated current, the dropout voltage for that current scales accordingly. The following equation calculates the $R_{DS(ON)}$ of the device.

$$R_{DS(ON)} = \frac{V_{DO}}{I_{RATED}} \quad (1)$$


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### 7.3.3 Foldback Current Limit

The device has an internal current limit circuit that protects the regulator during transient high-load current faults or shorting events. The current limit is a hybrid brick-wall-foldback scheme. The current limit transitions from a brick-wall scheme to a foldback scheme at the foldback voltage ($V_{FOLDBACK}$). In a high-load current fault with the output voltage above $V_{FOLDBACK}$, the brick-wall scheme limits the output current to the current limit ($I_{CL}$). When the voltage drops below $V_{FOLDBACK}$, a foldback current limit activates that scales back the current as the output voltage approaches GND. When the output is shorted, the device supplies a typical current called the short-circuit current limit ($I_{SC}$). $I_{CL}$ and $I_{SC}$ are listed in the *Electrical Characteristics* table.

For this device, $V_{FOLDBACK}$ = 50% × $V_{OUT(nom)}$.

The output voltage is not regulated when the device is in current limit. When a current limit event occurs, the device begins to heat up because of the increase in power dissipation. When the device is in brick-wall current limit, the pass transistor dissipates power [($V_{IN}$ – $V_{OUT}$) × $I_{CL}$]. When the device output is shorted and the output is below $V_{FOLDBACK}$, the pass transistor dissipates power [($V_{IN}$ – $V_{OUT}$) × $I_{SC}$]. If thermal shutdown is triggered, the device turns off. After the device cools down, the internal thermal shutdown circuit turns the device back on. If the output current fault condition continues, the device cycles between current limit and thermal shutdown. For more information on current limits, see the *Know Your Limits* application note.

图 7-3 shows a diagram of the foldback current limit.

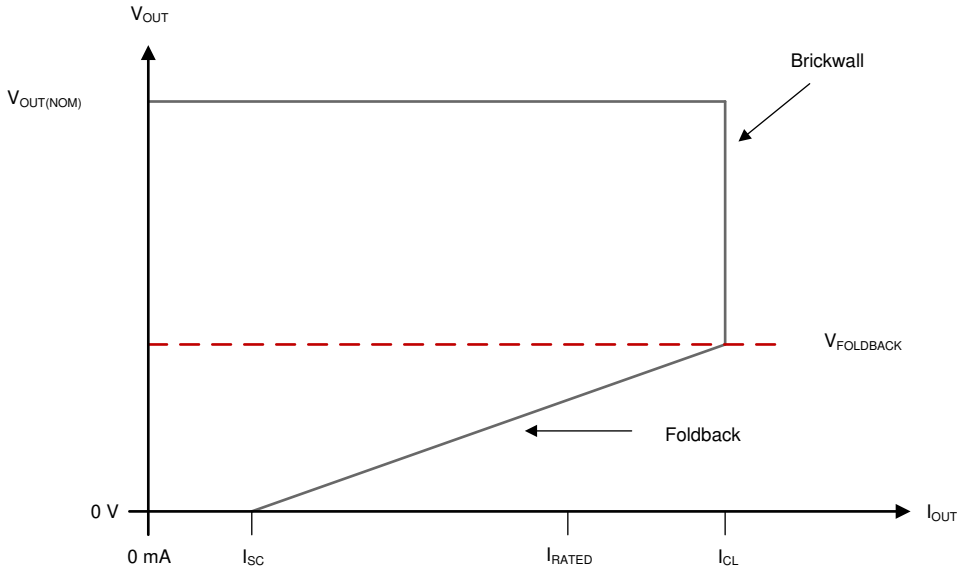



**图 7-3. Foldback Current Limit**

### 7.3.4 Undervoltage Lockout (UVLO)

The device has an independent undervoltage lockout (UVLO) circuit that monitors the input voltage, allowing a controlled and consistent turn on and off of the output voltage. To prevent the device from turning off if the input drops during turn on, the UVLO has hysteresis as specified in the *Electrical Characteristics* table.

### 7.3.5 Output Pulldown

The device has an output pulldown circuit. $V_{OUT}$ pulldown sink to ground capability is listed in the *Electrical Characteristics* table. The output pulldown activates under the following conditions:

- Device disabled

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- 1.0 V < $V_{IN}$ < $V_{UVLO}$

The output pulldown current for this device is 1.2 mA typical, as listed in the *Electrical Characteristics* table of the *Specifications* section.

Do not rely on the output pulldown circuit for discharging a large amount of output capacitance after the input supply has collapsed because reverse current can flow from the output to the input. This reverse current flow can cause damage to the device. See the *Reverse Current* section for more details.

### 7.3.6 Thermal Shutdown

The device contains a thermal shutdown protection circuit to disable the device when the junction temperature ($T_J$) of the pass transistor rises to $T_{SD(shutdown)}$ (typical). Thermal shutdown hysteresis assures that the device resets (turns on) when the temperature falls to $T_{SD(reset)}$ (typical).

The thermal time-constant of the semiconductor die is fairly short, thus the device may cycle on and off when thermal shutdown is reached until power dissipation is reduced. Power dissipation during start-up can be high from large $V_{IN}$ – $V_{OUT}$ voltage drops across the device or from high inrush currents charging large output capacitors. Under some conditions, the thermal shutdown protection disables the device before start-up completes.

For reliable operation, limit the junction temperature to the maximum listed in the *Recommended Operating Conditions* table. Operation above this maximum temperature causes the device to exceed its operational specifications. Although the internal protection circuitry of the device is designed to protect against thermal overall conditions, this circuitry is not intended to replace proper heat sinking. Continuously running the device into thermal shutdown or above the maximum recommended junction temperature reduces long-term reliability.


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## 7.4 Device Functional Modes

### 7.4.1 Device Functional Mode Comparison

表 7-1 shows the conditions that lead to the different modes of operation. See the *Electrical Characteristics* table for parameter values.

**表 7-1. Device Functional Mode Comparison**

| OPERATING MODE | PARAMETER | | | |
|---|---|---|---|---|
| | $V_{IN}$ | $V_{EN}$ | $I_{OUT}$ | $T_J$ |
| Normal operation | $V_{IN} > V_{OUT(nom)} + V_{DO}$ and $V_{IN} > V_{IN(min)}$ | $V_{EN} > V_{EN(HI)}$ | $I_{OUT} < I_{OUT(max)}$ | $T_J < T_{SD(shutdown)}$ |
| Dropout operation | $V_{IN(min)} < V_{IN} < V_{OUT(nom)} + V_{DO}$ | $V_{EN} > V_{EN(HI)}$ | $I_{OUT} < I_{OUT(max)}$ | $T_J < T_{SD(shutdown)}$ |
| Disabled (any true condition disables the device) | $V_{IN} < V_{UVLO}$ | $V_{EN} < V_{EN(LOW)}$ | Not applicable | $T_J > T_{SD(shutdown)}$ |

### 7.4.2 Normal Operation

The device regulates to the nominal output voltage when the following conditions are met:

- The input voltage is greater than the set MID_OUT output voltage plus the $V_{MID_OUT}$ dropout voltage ($V_{MID_OUT(nom)} + V_{DO(MID_OUT)}$)
- The current sourced from OUT or MID_OUT is less than the current limits ($I_{OUT} < I_{CL(OUT)}$ or $I_{MID_OUT} < I_{CL(MID_OUT)}$) respectively
- The device junction temperature is less than the thermal shutdown temperature ($T_J < T_{SD}$)
- The enable voltage has previously exceeded the enable rising threshold voltage and has not yet decreased to less than the enable falling threshold or the EN pin is left floating

### 7.4.3 Dropout Operation

If the input voltage is lower than the set MID_OUT voltage plus the specified $V_{DO(MID_OUT)}$ dropout voltage, but all other conditions are met for normal operation, the device operates in $V_{MID_OUT}$ dropout mode. When the device operates in this mode while $V_{MID_OUT}$ voltage is still higher than $V_{OUT(nom)} + V_{DO(OUT)}$, then $V_{OUT}$ is still in regulation however $V_{MID_OUT}$ voltage is in its dropout mode. In $V_{MID_OUT}$ dropout mode, $V_{MID_OUT}$ voltage tracks the input voltage and during this mode, the transient performance of $V_{MID_OUT}$ voltage becomes significantly degraded because the MID_OUT pass transistor is in the ohmic or triode region, and acts as a switch. Also $V_{MID_OUT}$ line or load transients can result in large $V_{MID_OUT}$ voltage deviations.

The device enters $V_{DO(OUT)}$ dropout mode when the input voltage is lower than the set MID_OUT voltage and $V_{MID_OUT}$ is lower than $V_{OUT(nom) + VDO(OUT)}$. In $V_{OUT}$ dropout mode, $V_{OUT}$ voltage tracks $V_{MID_OUT}$ voltage which in return tracks the input voltage. During this mode, the transient performance of both $V_{MID_OUT}$ and $V_{OUT}$ voltages becomes significantly degraded because the pass transistors are in the ohmic or triode region and acting as switches. Also line or load transients can result in large $V_{MID_OUT}$ and $V_{OUT}$ voltages deviations.

When the device is in a steady dropout state (defined as when the device is in dropout, $V_{IN} < V_{OUT(NOM)} + V_{DO}$, directly after being in a normal regulation state, but *not* during start-up), the pass transistor is driven into the ohmic or triode region. When the input voltage returns to a value greater than or equal to the nominal output voltage plus the dropout voltage ($V_{OUT(NOM)} + V_{DO}$), the output voltage can overshoot for a short period of time while the device pulls the pass transistor back into the linear region.

### 7.4.4 Disabled

The output of the device can be shutdown by forcing the voltage of the enable pin to less than the maximum EN pin low-level input voltage (see the *Electrical Characteristics* table). When disabled, the pass transistor is turned off, internal circuits are shutdown, and the output voltage is actively discharged to ground by an internal discharge circuit from the output to ground.

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# 8 Application and Implementation

**备注**

以下应用部分中的信息不属于 TI 器件规格的范围，TI 不担保其准确性和完整性。TI 的客 户应负责确定器件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

## 8.1 Application Information

### 8.1.1 Adjustable Device Feedback Resistors

The adjustable-version device requires external feedback divider resistors to set the output voltage. $V_{OUT}$ is set using the feedback divider resistors, $R_1$ and $R_2$, according to the following equation:

$$V_{OUT} = V_{FB} \times (1 + R_1 / R_2) \quad (2)$$

To ignore the FB pin current error term in the $V_{OUT}$ equation, set the feedback divider current to 100x the FB pin current listed in the *Electrical Characteristics* table. This setting provides the maximum feedback divider series resistance, as shown in the following equation:

$$R_1 + R_2 \leqslant V_{OUT} / (I_{FB} \times 100) \quad (3)$$

### 8.1.2 Recommended Capacitor Types

The device is designed to be stable using low equivalent series resistance (ESR) ceramic capacitors at the input and output. Multilayer ceramic capacitors have become the industry standard for these types of applications and are recommended, but must be used with good judgment. Ceramic capacitors that employ X7R-, X5R-, and C0G-rated dielectric materials provide relatively good capacitive stability across temperature, whereas the use of Y5V-rated capacitors is discouraged because of large variations in capacitance.

Regardless of the ceramic capacitor type selected, the effective capacitance varies with operating voltage and temperature. As a rule of thumb, expect the effective capacitance to decrease by as much as 50%. The input and output capacitors recommended in the *Recommended Operating Conditions* table account for an effective capacitance of approximately 50% of the nominal value.

### 8.1.3 Input and Output Capacitor Requirements

Although an input capacitor is not required for stability, good analog design practice is to connect a capacitor from IN to GND. This capacitor counteracts reactive input sources and improves transient response, input ripple, and PSRR. An input capacitor is recommended if the source impedance is more than 0.5 Ω. A higher value capacitor may be necessary if large, fast rise-time load or line transients are anticipated or if the device is located several inches from the input power source.

Dynamic performance of the device is improved with the use of an output capacitor. Use an output capacitor within the range specified in the *Recommended Operating Conditions* table for stability.

### 8.1.4 Reverse Current

Excessive reverse current can damage this device. Reverse current flows through the intrinsic body diode of the pass transistor instead of the normal conducting channel. At high magnitudes, this current flow degrades the long-term reliability of the device.

Conditions where reverse current can occur are outlined in this section, all of which can exceed the absolute maximum rating of $V_{OUT} \leqslant V_{IN}$ + 0.3 V.

- If the device has a large $C_{OUT}$ and the input supply collapses with little or no load current
- The output is biased when the input supply is not established
- The output is biased above the input supply


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If reverse current flow is expected in the application, external protection is recommended to protect the device. Reverse current is not limited in the device, so external limiting is required if extended reverse voltage operation is anticipated.

图 8-1 shows one approach for protecting the device.

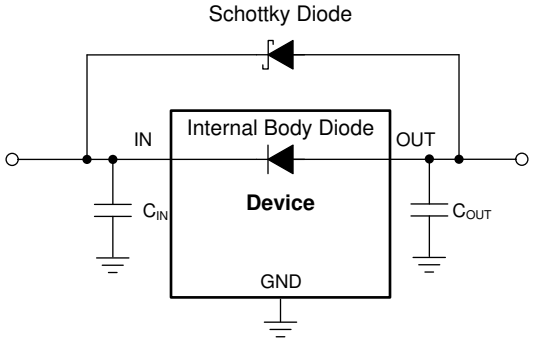



**图 8-1. Example Circuit for Reverse Current Protection Using a Schottky Diode**

### 8.1.5 Feed-Forward Capacitor ($C_{FF}$)

For the adjustable-voltage version device, a feed-forward capacitor ($C_{FF}$) can be connected from the OUT pin to the FB pin. $C_{FF}$ improves transient, noise, and PSRR performance, but is not required for regulator stability. Recommended $C_{FF}$ values are listed in the *Recommended Operating Conditions* table. A higher capacitance $C_{FF}$ can be used; however, the startup time increases. For a detailed description of $C_{FF}$ tradeoffs, see the *Pros and Cons of Using a Feedforward Capacitor with a Low-Dropout Regulator* application report.

$C_{FF}$ and $R_1$ form a zero in the loop gain at frequency $f_Z$, while $C_{FF}$, $R_1$, and $R_2$ form a pole in the loop gain at frequency $f_P$. $C_{FF}$ zero and pole frequencies can be calculated from the following equations:

$$f_Z = 1 / (2 \times \pi \times C_{FF} \times R_1) \quad (4)$$

$$f_P = 1 / (2 \times \pi \times C_{FF} \times (R_1 \parallel R_2)) \quad (5)$$

$C_{FF} \geq 10$ pF is required for stability if the feedback divider current is less than 5 µA. 方程式 6 calculates the feedback divider current.

$$I_{FB_Divider} = V_{OUT} / (R_1 + R_2) \quad (6)$$

To avoid startup time increases from $C_{FF}$, limit the product $C_{FF} \times R_1 < 50$ µs.

For an output voltage of 0.8 V with the FB pin tied to the OUT pin, no $C_{FF}$ is used.

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### 8.1.6 Power Dissipation ($P_D$)

Circuit reliability requires consideration of the device power dissipation, location of the circuit on the printed circuit board (PCB), and correct sizing of the thermal plane. The PCB area around the regulator must have few or no other heat-generating devices that cause added thermal stress.

To first-order approximation, power dissipation in the regulator depends on the input-to-output voltage difference and load conditions. The following equation calculates power dissipation ($P_D$).

$$P_D = (V_{IN} - V_{OUT}) \times I_{OUT} \quad (7)$$

**备注**

Power dissipation can be minimized, and therefore greater efficiency can be achieved, by correct selection of the system voltage rails. For the lowest power dissipation use the minimum input voltage required for correct output regulation.

For devices with a thermal pad, the primary heat conduction path for the device package is through the thermal pad to the PCB. Solder the thermal pad to a copper pad area under the device. This pad area must contain an array of plated vias that conduct heat to additional copper planes for increased heat dissipation.

The maximum power dissipation determines the maximum allowable ambient temperature ($T_A$) for the device. According to the following equation, power dissipation and junction temperature are most often related by the junction-to-ambient thermal resistance ($R_{\theta JA}$) of the combined PCB and device package and the temperature of the ambient air ($T_A$).

$$T_J = T_A + (R_{\theta JA} \times P_D) \quad (8)$$

Thermal resistance ($R_{\theta JA}$) is highly dependent on the heat-spreading capability built into the particular PCB design, and therefore varies according to the total copper area, copper weight, and location of the planes. The junction-to-ambient thermal resistance listed in the *Thermal Information* table is determined by the JEDEC standard PCB and copper-spreading area, and is used as a relative measure of package thermal performance.

### 8.1.7 Estimating Junction Temperature

The JEDEC standard now recommends the use of psi ($\Psi$) thermal metrics to estimate the junction temperatures of the linear regulator when in-circuit on a typical PCB board application. These metrics are not thermal resistance parameters and instead offer a practical and relative way to estimate junction temperature. These psi metrics are determined to be significantly independent of the copper area available for heat-spreading. The *Thermal Information* table lists the primary thermal metrics, which are the junction-to-top characterization parameter ($\psi_{JT}$) and junction-to-board characterization parameter ($\psi_{JB}$). These parameters provide two methods for calculating the junction temperature ($T_J$), as described in the following equations. Use the junction-to-top characterization parameter ($\psi_{JT}$) with the temperature at the center-top of device package ($T_T$) to calculate the junction temperature. Use the junction-to-board characterization parameter ($\psi_{JB}$) with the PCB surface temperature 1 mm from the device package ($T_B$) to calculate the junction temperature.

$$T_J = T_T + \psi_{JT} \times P_D \quad (9)$$

where:

- $P_D$ is the dissipated power
- $T_T$ is the temperature at the center-top of the device package

$$T_J = T_B + \psi_{JB} \times P_D \quad (10)$$

where:

- $T_B$ is the PCB surface temperature measured 1 mm from the device package and centered on the package edge


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For detailed information on the thermal metrics and how to use them, see the *Semiconductor and IC Package Thermal Metrics* application report

## 8.2 Typical Application

This section discusses implementing this device for a typical application. 图 8-2 shows the application circuit.

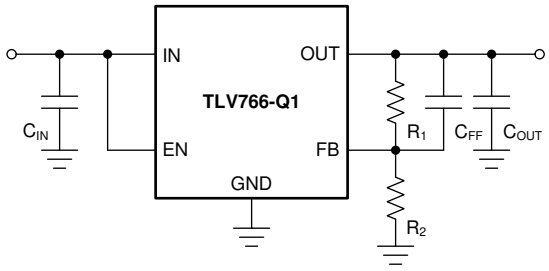



**图 8-2. Typical Application Circuit**

### 8.2.1 Design Requirements

表 8-1 summarizes the design requirements for this application.

**表 8-1. Design Parameters**

| PARAMETER | DESIGN REQUIREMENT |
|---|---|
| Input voltage | 5 V |
| Output voltage | 3.3 V |
| Output current | 100 mA |

### 8.2.2 Detailed Design Procedure

#### *8.2.2.1 Transient Response*

As with any regulator, increasing the size of the output capacitor reduces overshoot and undershoot magnitude. If load transients are expected with ramp rates greater than 0.5 A/µs, use a 2.2-µF or larger output capacitor.

#### *8.2.2.2 Choose Feedback Resistors*

For this design example, $V_{OUT}$ is set to 3.3 V. The following equations set the feedback divider resistors for the desired output voltage:

$$V_{OUT} = V_{FB} \times (1 + R_1 / R_2) \quad (11)$$

$$R_1 + R_2 \leqslant V_{OUT} / (I_{FB} \times 100) \quad (12)$$

For improved output accuracy, use 方程式 12 and $I_{FB}$ = 50 nA as listed in the *Electrical Characteristics* table in the *Specifications* section to calculate the upper limit for series feedback resistance ($R_1 + R_2 \leqslant 660$ kΩ).

The control-loop error amplifier drives the FB pin to the same voltage as the internal reference ($V_{FB}$ = 0.8 V, as listed in the *Electrical Characteristics* table). Use 方程式 11 to determine the ratio of $R_1 / R_2 = 3.125$. Use this ratio and solve 方程式 12 for $R_2$. Now calculate the upper limit for $R_2 \leqslant 160$ kΩ. Select a standard value resistor for $R_2$ = 160 kΩ.

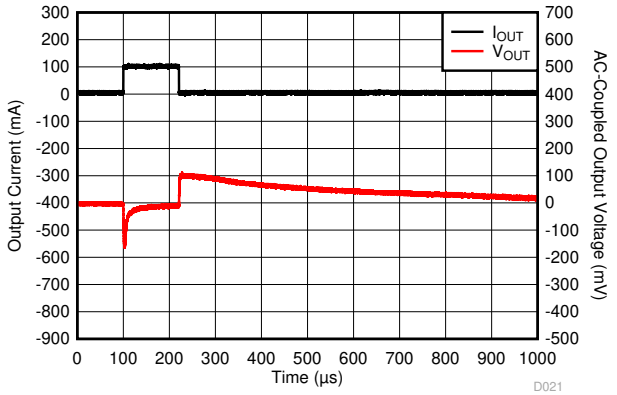
Reference 方程式 11 and solve for $R_1$:

$$R_1 = (V_{OUT} / V_{FB} - 1) \times R_2 \quad (13)$$

From 方程式 13, $R_1$ = 500 kΩ can be determined. Select a standard value resistor for $R_1$ = 499 kΩ. $V_{OUT}$ = 3.3 V (as determined by 方程式 11).

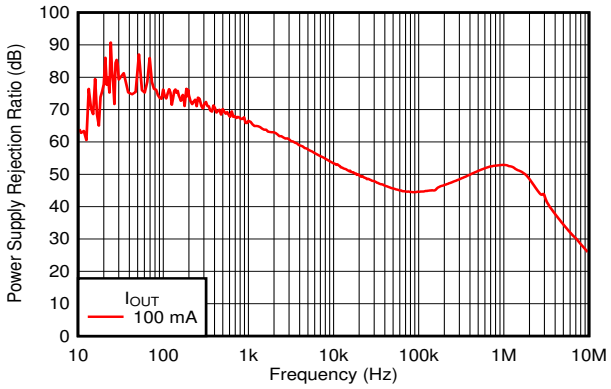
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### 8.2.3 Application Curves




$V_{IN}$ = 5 V, $V_{OUT}$ = 3.3 V, $C_{OUT}$ = 1 µF, $C_{FF}$ = 10 pF

**图 8-3. Load Transient Response, $I_{OUT}$ 0 mA to 100 mA**




$V_{IN}$ = 5 V, $V_{OUT}$ = 3.3 V, $C_{OUT}$ = 1 µF, $C_{FF}$ = 0 pF

**图 8-4. PSRR Performance**

## 8.3 Power Supply Recommendations

This device is designed to operate from an input supply voltage range of 2.5 V to 16 V. To ensure that the output voltage is well regulated and dynamic performance is optimum, the input supply must be at least $V_{OUT(nom)}$ + 1.5 V or 2.5 V, whichever is greater. Connect a low output impedance power supply directly to the input pin of the TLV766-Q1.


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## 8.4 Layout

### 8.4.1 Layout Guidelines

- Place input and output capacitors as close to the device as possible
- Use copper planes for device connections to IN, OUT, and GND pins to optimize thermal performance
- Place thermal vias around the device to distribute heat

### 8.4.2 Layout Examples

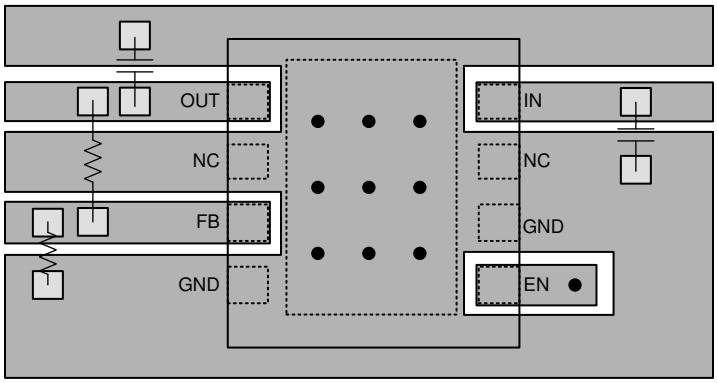



图 8-5. Layout Example for the Adjustable Version

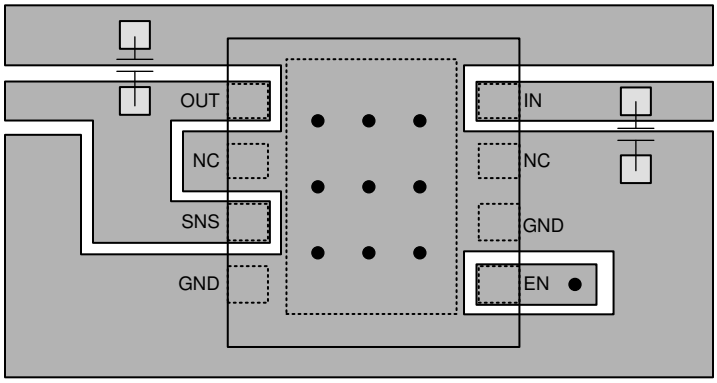



图 8-6. Layout Example for the Fixed Version

# 9 Device and Documentation Support

## 9.1 Device Support

### 9.1.1 Device Nomenclature

表 9-1. Available Options(1)

| PRODUCT | $V_{OUT}$ |
|---|---|
| TLV766**xx(x)QWyyyRQ1** | **xx(x)** is the nominal output voltage. For output voltages with a resolution of 100 mV, two digits are used in the ordering number; otherwise, three digits are used (for example, 33 = 3.3 V; 125 = 1.25 V). 01 indicates the adjustable output version.<br>**W** indicates a wettable flanks package.<br>**yyy** is the package designator.<br>**R** is the package quantity. R is for the large quantity reel. |

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or visit the device product folder at www.ti.com.

## 9.2 Documentation Support

### 9.2.1 Related Documentation

For related documentation see the following:

- Texas Instruments, *TLV767EVM-014 Evaluation Module* user's guide
- Texas Instruments, *Pros and Cons of Using a Feedforward Capacitor with a Low-Dropout Regulator* application report
- Texas Instruments, *Know Your Limits* application report
- Texas Instruments, *Universal Low-Dropout (LDO) Linear Voltage Regulator MultiPkgLDOEVM-823 Evaluation Module* user's guide

## 9.3 接收文档更新通知

要接收文档更新通知，请导航至 ti.com 上的器件产品文件夹。点击*订阅更新* 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

## 9.4 支持资源

TI E2E™ 支持论坛是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《使用条款》。

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ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

## 9.7 术语表

TI 术语表　　本术语表列出并解释了术语、首字母缩略词和定义。


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## 10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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## PACKAGING INFORMATION

| Orderable part number | Status (1) | Material type (2) | Package \| Pins | Package qty \| Carrier | RoHS (3) | Lead finish/ Ball material (4) | MSL rating/ Peak reflow (5) | Op temp (°C) | Part marking (6) |
|---|---|---|---|---|---|---|---|---|---|
| TLV76601QWDRBRQ1 | Active | Production | SON (DRB) \| 8 | 3000 \| LARGE T&R | Yes | NIPDAU | Level-2-260C-1 YEAR | -40 to 150 | V76601 |
| TLV76601QWDRBRQ1.A | Active | Production | SON (DRB) \| 8 | 3000 \| LARGE T&R | Yes | NIPDAU | Level-2-260C-1 YEAR | -40 to 150 | V76601 |
| TLV76612QWDRBRQ1 | Active | Production | SON (DRB) \| 8 | 3000 \| LARGE T&R | Yes | NIPDAU | Level-2-260C-1 YEAR | -40 to 150 | V76612 |
| TLV76612QWDRBRQ1.A | Active | Production | SON (DRB) \| 8 | 3000 \| LARGE T&R | Yes | NIPDAU | Level-2-260C-1 YEAR | -40 to 150 | V76612 |
| TLV76618QWDRBRQ1 | Active | Production | SON (DRB) \| 8 | 3000 \| LARGE T&R | Yes | NIPDAU | Level-2-260C-1 YEAR | -40 to 150 | V76618 |
| TLV76618QWDRBRQ1.A | Active | Production | SON (DRB) \| 8 | 3000 \| LARGE T&R | Yes | NIPDAU | Level-2-260C-1 YEAR | -40 to 150 | V76618 |
| TLV76633QWDRBRQ1 | Active | Production | SON (DRB) \| 8 | 3000 \| LARGE T&R | Yes | NIPDAU | Level-2-260C-1 YEAR | -40 to 150 | V76633 |
| TLV76633QWDRBRQ1.A | Active | Production | SON (DRB) \| 8 | 3000 \| LARGE T&R | Yes | NIPDAU | Level-2-260C-1 YEAR | -40 to 150 | V76633 |
| TLV76650QWDRBRQ1 | Active | Production | SON (DRB) \| 8 | 3000 \| LARGE T&R | Yes | NIPDAU | Level-2-260C-1 YEAR | -40 to 150 | V76650 |
| TLV76650QWDRBRQ1.A | Active | Production | SON (DRB) \| 8 | 3000 \| LARGE T&R | Yes | NIPDAU | Level-2-260C-1 YEAR | -40 to 150 | V76650 |

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

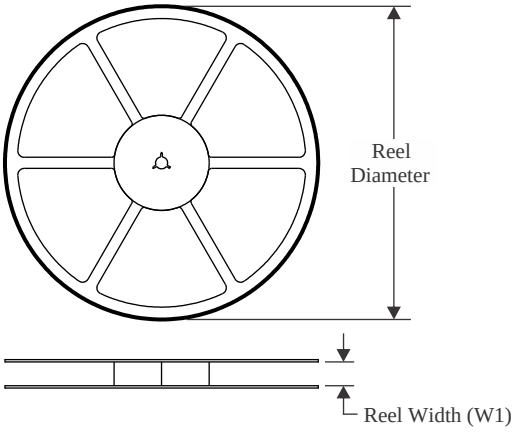
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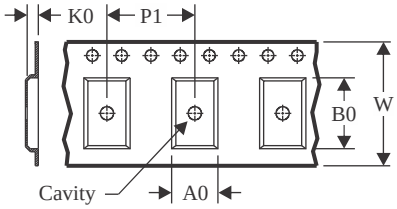
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## TAPE AND REEL INFORMATION

**REEL DIMENSIONS**

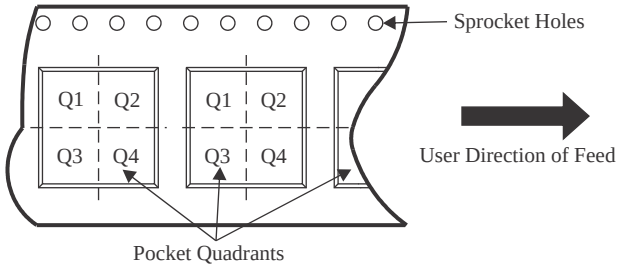



**TAPE DIMENSIONS**




| | |
|---|---|
| A0 | Dimension designed to accommodate the component width |
| B0 | Dimension designed to accommodate the component length |
| K0 | Dimension designed to accommodate the component thickness |
| W | Overall width of the carrier tape |
| P1 | Pitch between successive cavity centers |

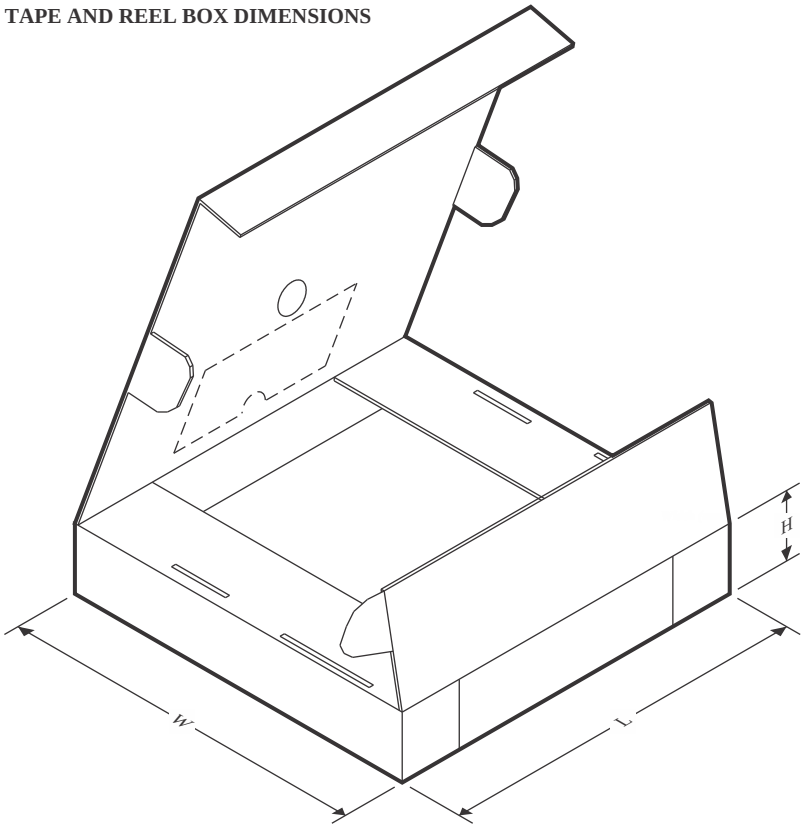
**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**




*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|---|---|---|---|---|---|---|---|---|---|---|---|---|
| TLV76601QWDRBRQ1 | SON | DRB | 8 | 3000 | 330.0 | 12.4 | 3.3 | 3.3 | 1.1 | 8.0 | 12.0 | Q2 |
| TLV76612QWDRBRQ1 | SON | DRB | 8 | 3000 | 330.0 | 12.4 | 3.3 | 3.3 | 1.1 | 8.0 | 12.0 | Q2 |
| TLV76618QWDRBRQ1 | SON | DRB | 8 | 3000 | 330.0 | 12.4 | 3.3 | 3.3 | 1.1 | 8.0 | 12.0 | Q2 |
| TLV76633QWDRBRQ1 | SON | DRB | 8 | 3000 | 330.0 | 12.4 | 3.3 | 3.3 | 1.1 | 8.0 | 12.0 | Q2 |
| TLV76650QWDRBRQ1 | SON | DRB | 8 | 3000 | 330.0 | 12.4 | 3.3 | 3.3 | 1.1 | 8.0 | 12.0 | Q2 |

TAPE AND REEL BOX DIMENSIONS




*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
|---|---|---|---|---|---|---|---|
| TLV76601QWDRBRQ1 | SON | DRB | 8 | 3000 | 367.0 | 367.0 | 35.0 |
| TLV76612QWDRBRQ1 | SON | DRB | 8 | 3000 | 367.0 | 367.0 | 35.0 |
| TLV76618QWDRBRQ1 | SON | DRB | 8 | 3000 | 367.0 | 367.0 | 35.0 |
| TLV76633QWDRBRQ1 | SON | DRB | 8 | 3000 | 367.0 | 367.0 | 35.0 |
| TLV76650QWDRBRQ1 | SON | DRB | 8 | 3000 | 367.0 | 367.0 | 35.0 |

## GENERIC PACKAGE VIEW

# DRB 8

# VSON - 1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD




Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

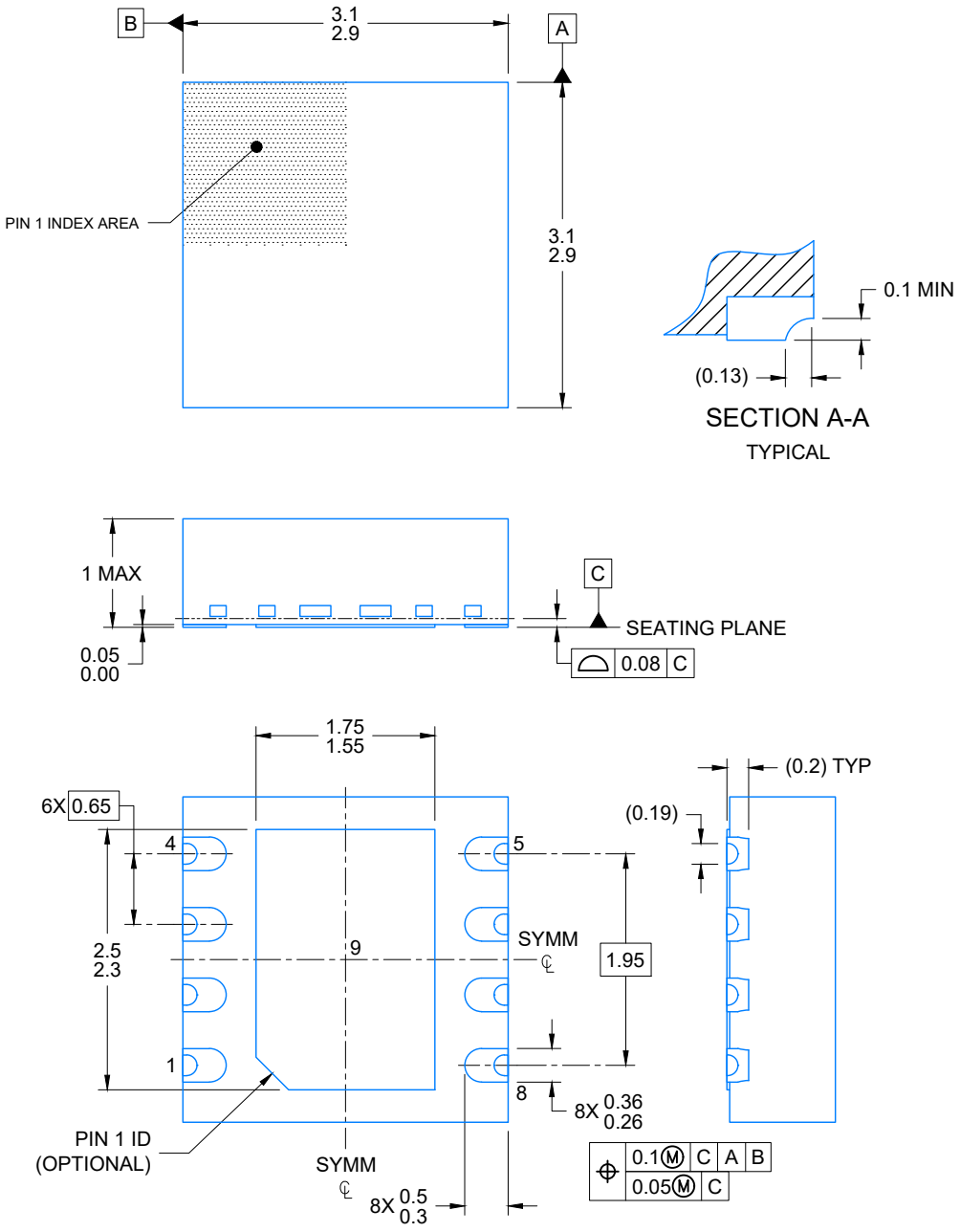
4203482/L

# PACKAGE OUTLINE

## DRB0008J

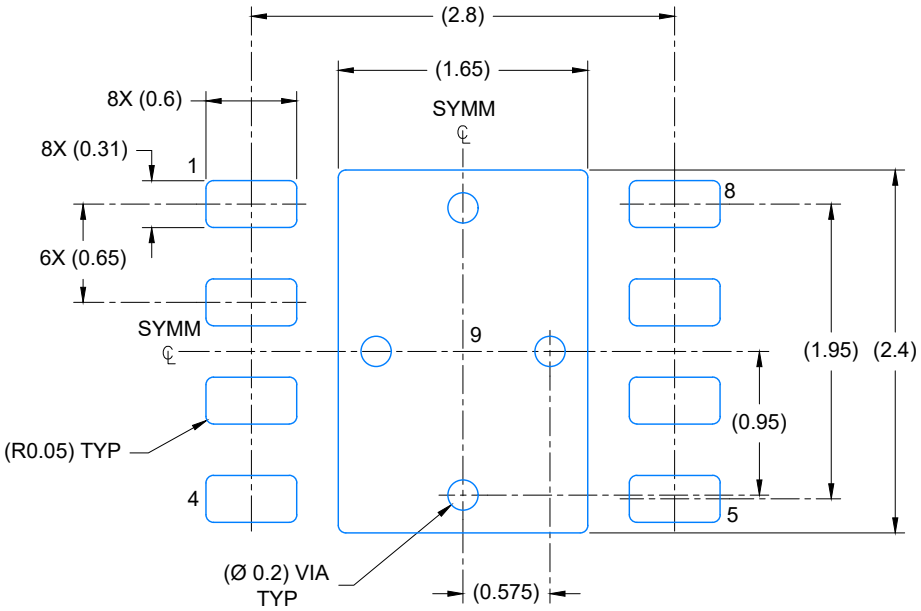
## VSON - 1 mm max height

PLASTIC QUAD FLAT PACK- NO LEAD

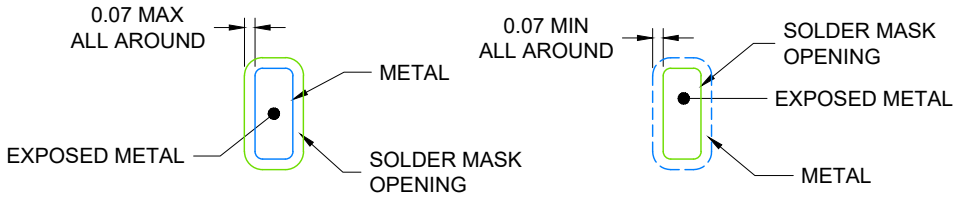



NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.




LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X




NON- SOLDER MASK
DEFINED
(PREFERRED)

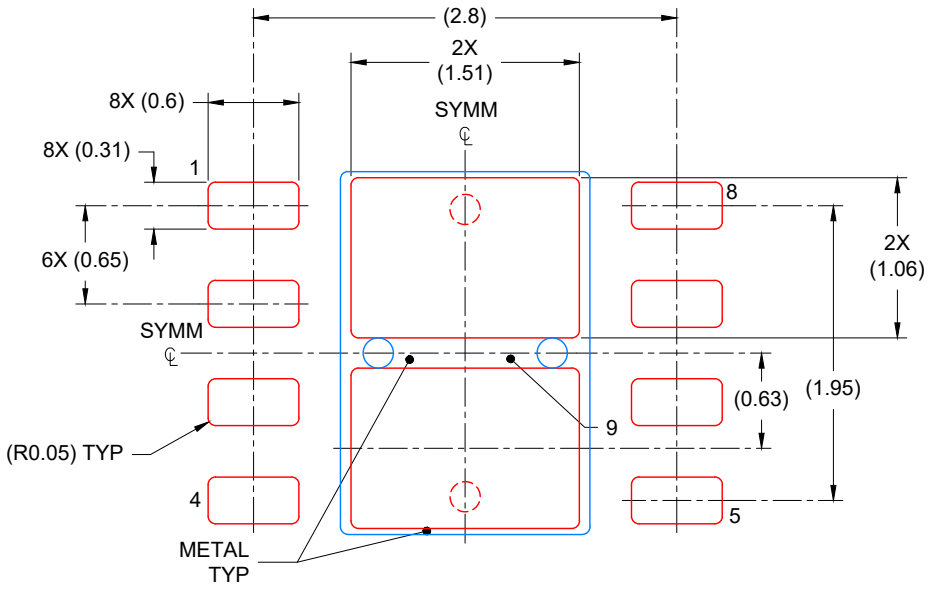
SOLDER MASK
DEFINED

SOLDER MASK DETAILS

4225036/A 06/2019

NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.




SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD
81% PRINTED COVERAGE BY AREA
SCALE: 20X

4225036/A 06/2019

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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最后更新日期：2025 年 10 月